

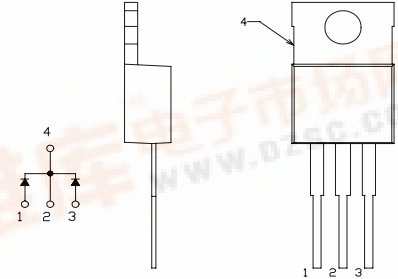


# SBD Type : GCQ30A04

OUTLINE DRAWING

## FEATURES

- \*Similar to TO-220AB Case
- \*Dual Diodes – Cathode Common
- \*Low Forward Voltage Drop
- \*High Surge Capability
- \*Tj=150 °C operation



## Maximum Ratings

Approx Net Weight: 1.9g

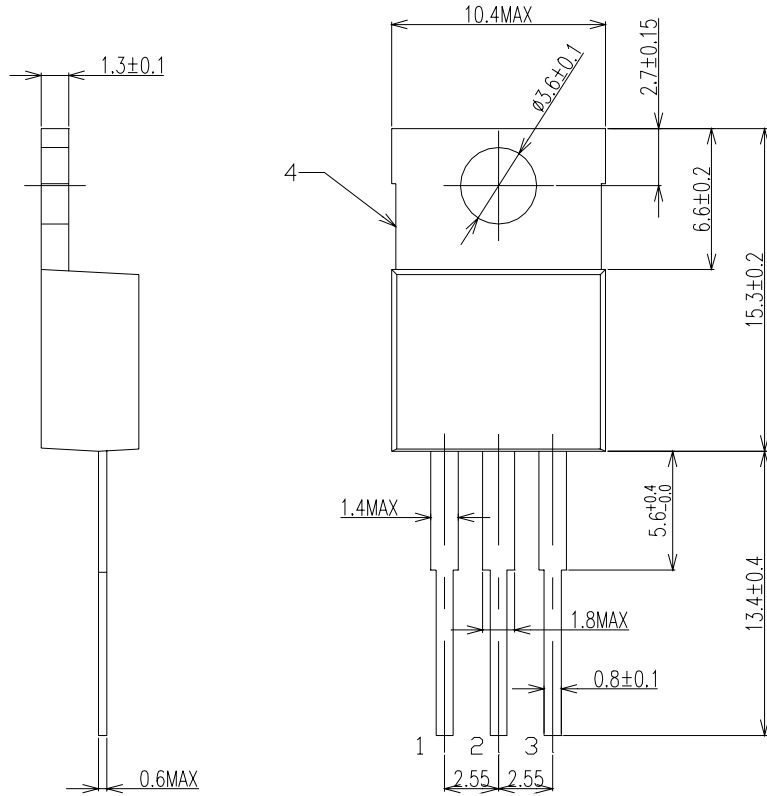
Rating	Symbol	GCQ30A04			Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	40			V
Average Rectified Output Current	$I_O$	30	$T_c=104^{\circ}C$	50 Hz Full Sine Wave Resistive Load	A
RMS Forward Current	$I_{F(RMS)}$	33.3			A
Surge Forward Current	$I_{FSM}$	250	50Hz Full Sine Wave ,1cycle Non-repetitive		A
Operating JunctionTemperature Range	$T_{jw}$	-40 to +150			°C
Storage Temperature Range	$T_{stg}$	-40 to +150			°C
Mounting torque	Ftor	recommended torque = 0.5			N•m

## Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	$I_{RM}$	$T_j= 25^{\circ}C, V_{RM}= V_{RRM}$ per arm	-	-	15	mA
Peak Forward Voltage	$V_{FM}$	$T_j= 25^{\circ}C, I_{FM}= 15 A$ per arm	-	-	0.55	V
Thermal Resistance	$R_{th(j-c)}$	Junction to Case	-	-	1.5	°C/W



GCQ30A04 OUTLINE DRAWING (Dimensions in mm)



Center Tap

